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SOT-23



MMBTRC116SS-MMBTRC122SS

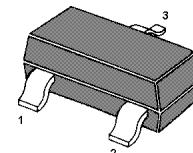
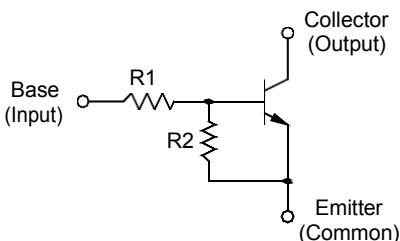
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NPN Silicon Epitaxial Planar Transistor

for switching, interface circuit and drive
circuit applications

Features

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process



1. Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Resistor Values

Type	R1 (KΩ)	R2 (KΩ)	MARKING
MMBTRC116SS	1	10	16BR
MMBTRC117SS	2.2	2.2	17BR
MMBTRC118SS	2.2	10	18BR
MMBTRC119SS	4.7	10	19BR
MMBTRC120SS	10	4.7	20BR
MMBTRC121SS	47	10	21BR
MMBTRC122SS	100	100	22BR

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Output Voltage	V_o	50	V
Input Voltage	V_i	10, - 5	V
		12, - 10	
		12, - 5	
		20, - 7	
		30, - 10	
		40, - 15	
		40, - 10	
Output Current	I_o	100	mA
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_s	- 55 to + 150	°C



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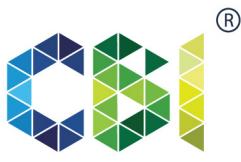
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Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_O = 5 \text{ V}$, $I_O = 5 \text{ mA}$ at $V_O = 5 \text{ V}$, $I_O = 20 \text{ mA}$ at $V_O = 5 \text{ V}$, $I_O = 10 \text{ mA}$ at $V_O = 5 \text{ V}$, $I_O = 10 \text{ mA}$ at $V_O = 5 \text{ V}$, $I_O = 10 \text{ mA}$ at $V_O = 5 \text{ V}$, $I_O = 5 \text{ mA}$ at $V_O = 5 \text{ V}$, $I_O = 5 \text{ mA}$	G_I	33	-	-	-
		20	-	-	-
		33	-	-	-
		30	-	-	-
		24	-	-	-
		33	-	-	-
		62	-	-	-
Output Cutoff Current at $V_O = 50 \text{ V}$	$I_{O(OFF)}$	-	-	500	nA
Input Current at $V_I = 5 \text{ V}$	I_I	-	-	7.2	mA
		-	-	3.8	
		-	-	3.8	
		-	-	1.8	
		-	-	0.88	
		-	-	0.16	
		-	-	0.15	
Output Voltage at $I_O = 10 \text{ mA}$, $I_I = 0.5 \text{ mA}$ at $I_O = 10 \text{ mA}$, $I_I = 0.5 \text{ mA}$ at $I_O = 10 \text{ mA}$, $I_I = 0.5 \text{ mA}$ at $I_O = 10 \text{ mA}$, $I_I = 0.5 \text{ mA}$ at $I_O = 10 \text{ mA}$, $I_I = 0.5 \text{ mA}$ at $I_O = 10 \text{ mA}$, $I_I = 0.5 \text{ mA}$ at $I_O = 5 \text{ mA}$, $I_I = 0.25 \text{ mA}$	$V_{O(ON)}$	-	-	0.3	V
		-	-	0.3	
		-	-	0.3	
		-	-	0.3	
		-	-	0.3	
		-	-	0.3	
		-	-	0.3	
Input Voltage (ON) at $V_O = 0.3 \text{ V}$, $I_O = 20 \text{ mA}$ at $V_O = 0.3 \text{ V}$, $I_O = 20 \text{ mA}$ at $V_O = 0.3 \text{ V}$, $I_O = 20 \text{ mA}$ at $V_O = 0.3 \text{ V}$, $I_O = 20 \text{ mA}$ at $V_O = 0.3 \text{ V}$, $I_O = 2 \text{ mA}$ at $V_O = 0.3 \text{ V}$, $I_O = 2 \text{ mA}$ at $V_O = 0.3 \text{ V}$, $I_O = 1 \text{ mA}$	$V_{I(ON)}$	-	-	3	V
		-	-	3	
		-	-	3	
		-	-	2.5	
		-	-	3	
		-	-	5	
		-	-	3	
Input Voltage (OFF) at $V_{CC} = 5 \text{ V}$, $I_O = 100 \mu\text{A}$	$V_{I(OFF)}$	0.3	-	-	V
		0.5	-	-	
		0.3	-	-	
		0.3	-	-	
		0.8	-	-	
		1	-	-	
		0.5	-	-	
Transition Frequency at $V_O = 10 \text{ V}$, $I_O = 5 \text{ mA}$	$f_T^{(1)}$	-	250	-	MHz

¹⁾ Characteristic of transistor only.



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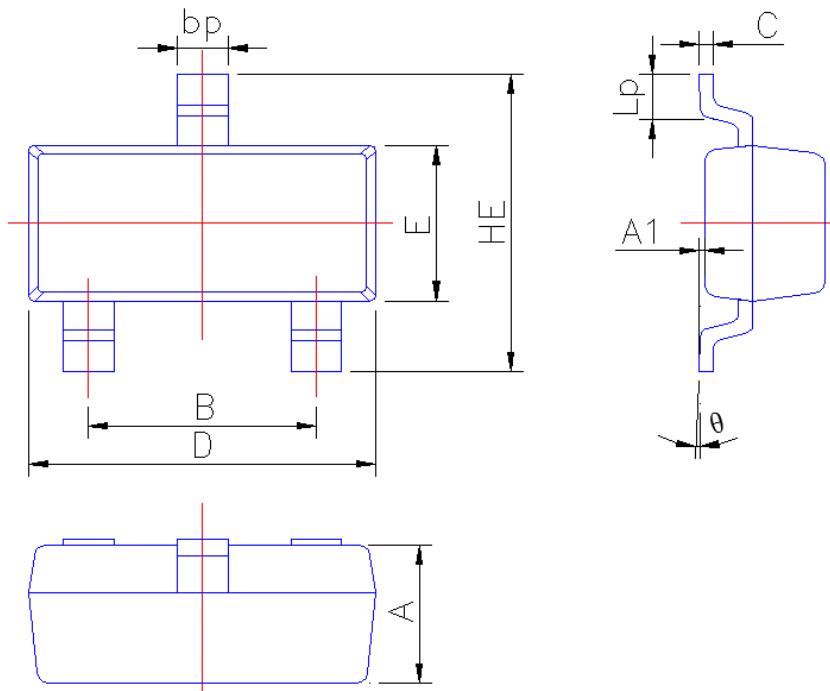
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

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Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.10
A1	0.013	0.100
B	1.80	2.00
bp	0.35	0.50
C	0.09	0.150
D	2.80	3.00
E	1.20	1.40
HE	2.20	2.80
Lp	0.20	0.50
θ	0°	5°